



40V PNP LOW VCESAT TRANSISTOR IN POWERDI3333-8

Features

- BV_{CEO} > -40V
- Small Form Factor Thermally Efficient Package.
 Enables Higher Density End Products
- I_C = -3A High Continuous Current
- I_{CM} = -6A Peak Pulse Current
- Low Saturation Voltage VCE(sat) < -400mV @ -1A
- Minimum hFE 200 @ Ic=-1A
- Rated to +175°C—Ideal For High Temperature Environment
- Wettable Flank For Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: PowerDI®3333-8
- Case Material: Molded Plastic. "Green" Molding Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Solderable per MIL-STD-202, Method 208 (©3)
- Weight: 0.03 grams (Approximate)

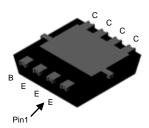
Applications

- High Side Switch
- Low Drop Out Regulator
- MOSFET or IGBT Gate Driving

PowerDI3333-8 (SWP) (Type UX)

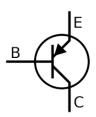


Top View



Bottom View

Equivalent Circuit



Device Symbol

Ordering Information (Note 4)

Ī	Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
	DXTP07040CFG-7	AEC-Q101	2G5	7	12	2,000

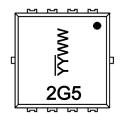
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- <1000ppm antimony compounds.

 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

PowerDI3333-8 (SWP) (Type UX)



2G5= Product Type Marking Code

\text{YYWW} = Date Code Marking

YY = Last Two Digits of Year (ex: 18 = 2018)

WW = Week Code (01 to 53)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	Ic	-3	Α
Peak Pulse Current	Ісм	-6	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
	(Note 5)		0.9	W
Power Dissipation	(Note 6)	P_{D}	2.1	W
	(Note 7)		3.1	W
	(Note 5)		140	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\Theta JA}$	65	°C/W
	(Note 7)		44	°C/W
Thermal Resistance, Junction to Leads (Note 8	R _{ÐJL}	8.5	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C	

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400	V	С

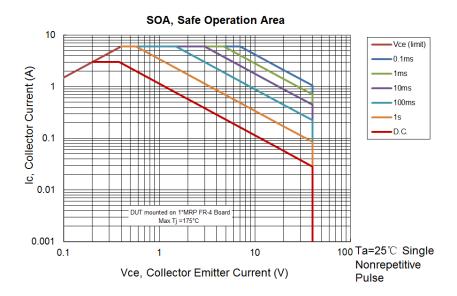
Notes:

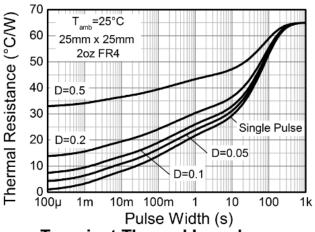
- 5. For a device mounted with the collector tab on MRP FR4-PCB; device is measured under still air conditions whilst operating in a steady-state.
 6. Same as Note 5, except the device is mounted on 25mm × 25mm 2oz copper.
 7. Same as Note 5, except the device is mounted on 50mm × 50mm 2oz copper.
 8. Thermal resistance from junction to solder-point (at the collector tab).
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

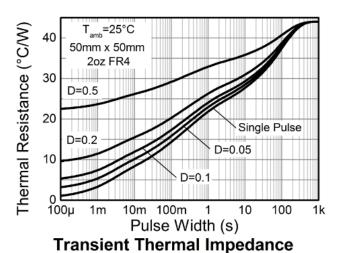
DXTP07040CFG Datasheet Number: DS41046 Rev. 1 - 2



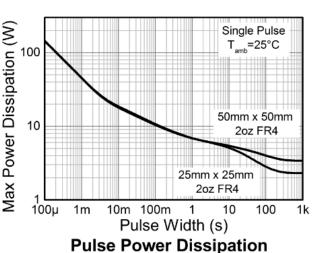
Thermal Characteristics and Derating Information







Transient Thermal Impedance



3.5 Max Power Dissipation (W) 50mm x 50mm 3.0 2oz FR4 2.5 2.0 25mm x 25mm 1.5 2oz FR4 1.0 0.5 20 60 80 100 120 140 Temperature (°C)

Derating Curve



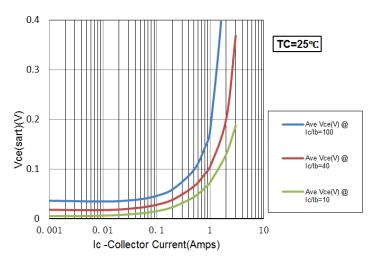
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

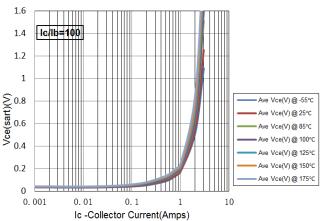
Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	-50	-65	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-40	-57	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	-8.8		V	I _E = -100μA
Collector Cut-Off Current		_	_	-20	nA	V _{CB} = -40V
Collector Cut-Oil Current	I _{CBO}	_	_	-10	μA	$V_{CB} = -40V, T_A = +125^{\circ}C$
Emitter Cut-Off Current	I _{EBO}	_	_	-20	nA	$V_{EB} = -6V$
	h _{FE}	300	527	800	_	$I_C = -10 \text{mA}, V_{CE} = -2 \text{V}$
DC Current Transfer Statio Patia (Note 10)		250	432	_	_	$I_C = -500 \text{mA}, V_{CE} = -2V$
DC Current Transfer Static Ratio (Note 10)		200	377	_	_	I _C = -1A, V _{CE} = -2V
		150	273	_	_	$I_C = -2A$, $V_{CE} = -2V$
	V _{CE(sat)}	_	-99	-200	mV	$I_C = -500 \text{mA}, I_B = -5 \text{mA}$
Collector-Emitter Saturation Voltage (Note 10)		_	-177	-400	mV	$I_C = -1A$, $I_B = -10mA$
		_	-200	-500	mV	$I_C = -2A$, $I_B = -50mA$
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	_	-0.8	-1	V	$I_C = -1A$, $I_B = -10mA$
Base-Emitter Turn-On Voltage (Note 10)	$V_{BE(on)}$	_	-0.75	0.9	V	$I_C = -1A$, $V_{CE} = -2V$
Transitional Frequency	f_{T}	100	_	_	MHz	$I_C = -50 \text{mA}, V_{CE} = -5 \text{V},$ f = 50 MHz
Output Capacitance	C _{obo}	_	24	_	pF	V _{CB} = -10V, f = 1MHz
Switching Time	toN	_	35	_	ns	$V_{CC} = -10V, I_{C} = -500mA,$
Switching Time	t _{OFF}	_	600	_	ns	$I_{B1} = -I_{B2} = -50 \text{mA}$

Note: 10. Measured under pulsed conditions. Pulse width \leqslant 300 μ s. Duty cycle \leqslant 2%.



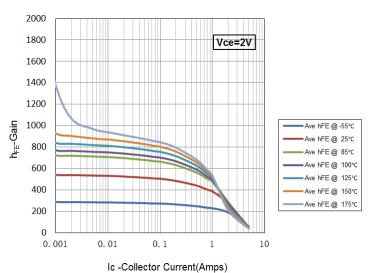
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)



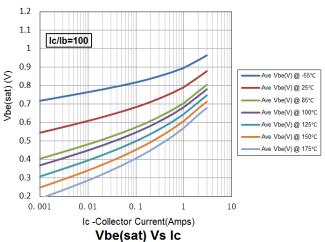


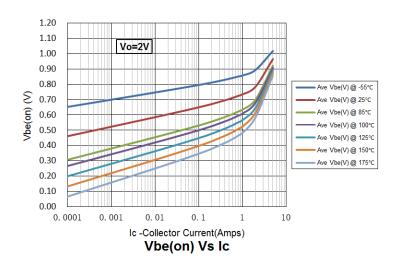
Vce(sat) Vs Ic

Vce(sat) Vs Ic



HFE Vs Ic



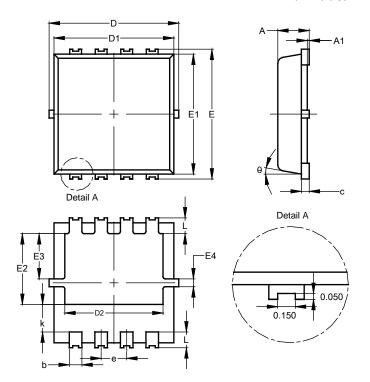




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

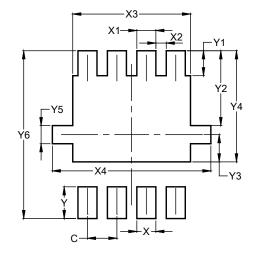


PowerDI3333-8 (SWP)						
(Type UX)						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	_			
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_	_	0.65			
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
Х3	2.600
X4	3.500
Υ	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700



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